

Amendments to the Specification:

Please replace the paragraph starting on line 9 of page 7 with the following amended paragraph:

-- In one embodiment, the magnesium oxide ("MgO") layer generally is formed to a thickness of 70-1,000 angstrom by a sputtering process using a pure magnesium target. The MgO layer is grown highly oriented on the amorphous gate oxide layer. During the sputtering step, the chamber is provided with an oxygen-bearing atmosphere such as argon/oxygen gas mixture and kept at a temperature of 400-500 Celsius. After deposition, the MgO layer is annealed for about 30 minutes in a temperature of 800-1,000 Celsius. The annealing step enhances the alignment of MgO crystallites in a highly oriented pattern. A ferroelectric layer to be deposited over the second buffer of MgO layer requires a highly oriented substrate to promote growth of a highly-oriented ferroelectric thereon. The annealing step is particularly useful when working with thin MgO layers since they are more likely to have amorphous or poorly oriented structures as deposited. Generally, the highly-oriented MgO and ferroelectric layers have polycrystalline structures. --